

Title (en)  
MOS TRANSISTOR WITH ADJUSTABLE THRESHOLD

Title (de)  
MOS-TRANSISTOR MIT EINSTELLBAREM GRENZWERT

Title (fr)  
TRANSISTOR MOS A SEUIL REGLABLE

Publication  
**EP 1994567 A2 20081126 (FR)**

Application  
**EP 07731623 A 20070214**

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Abstract (en)  
[origin: WO2007093741A2] The invention concerns a MOS transistor comprising a conductive extension (10) of its source region, isolated from its substrate, and extending partly under its channel.

IPC 8 full level  
**H01L 29/792** (2006.01); **H01L 21/336** (2006.01); **H01L 29/06** (2006.01)

CPC (source: EP US)  
**H01L 29/0653** (2013.01 - EP US); **H01L 29/1054** (2013.01 - EP US); **H01L 29/1083** (2013.01 - EP US); **H01L 29/66636** (2013.01 - EP US); **H01L 29/7841** (2013.01 - EP US); **H01L 29/792** (2013.01 - EP US); **H01L 29/7923** (2013.01 - EP US); **H01L 29/665** (2013.01 - EP US); **H01L 29/66833** (2013.01 - EP US)

Citation (search report)  
See references of WO 2007093741A2

Citation (examination)  
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Designated contracting state (EPC)  
FR GB

DOCDB simple family (publication)  
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**FR 2007050798 W 20070214**; EP 07731623 A 20070214; JP 2008553809 A 20070214; US 27905607 A 20070214